

IN THE SPECIFICATION:

Please replace the paragraph at page 4, lns. 10-21 with the following amended paragraph:

Amend the paragraph at page 4, lns. 10-21 as follows:

Reports related to a hydrogenated silicon oxynitride film manufactured by plasma CVD using SiH_4 , N_2O , and H_2 as raw material gasses, for example, Yeh, Jiun-Lin, and Lee, Si-Chen, Structural and Optical Properties of Amorphous Silicon Oxynitride, Journal of Applied Physics, vol. 79, no. 2, pp. 656-663, [[1966]] 1996, discuss a hydrogenated silicon oxynitride film manufactured by plasma CVD with a decomposition temperature of 250°C, and a mixture ratio of hydrogen (H_2) vs. SiH_4 + N_2O fixed at 0.9 to 1.0, in which the value of the mixture ratio X_g , expressed as $X_g = [\text{N}_2\text{O}] / ([\text{SiH}_4] + [\text{N}_2\text{O}])$, is changed from 0.05 to 0.975. However, the existence of HSi-O_3 bonds and $\text{H}_2\text{Si-O}_2$ bonds in the manufactured hydrogenated silicon oxynitride film is clearly observed by Fourier transform infrared spectroscopy (FT-IR). These kinds of bonds will completely degrade the thermal stability and, moreover, there is a fear that the change in the coordination number will form defect level densities in the periphery of the bonds. Therefore, even with the same hydrogenated silicon oxynitride film, if the composition, or components including impurity element, is not examined in detail, then it cannot carelessly be used for as an insulating film such as the gate insulating film which imparts critical influence to the TFT characteristics.